

Switch-mode Schottky Power Rectifier MBRF20200CTG

The Switch-mode Power Rectifier employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for use as rectifiers in very low-voltage, high-frequency switching power supplies, free wheeling diodes and polarity protection diodes.

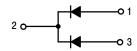
Features

- Highly Stable Oxide Passivated Junction
- Very Low Forward Voltage Drop
- Matched Dual Die Construction
- High Junction Temperature Capability
- High dv/dt Capability
- Guardring for Stress Protection
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Electrically Isolated. No Isolation Hardware Required.
- These Devices are Pb-Free and are RoHS Compliant

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

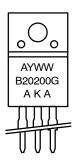
SCHOTTKY BARRIER RECTIFIER 20 AMPERES, 200 VOLTS





TO-220 FULLPAK™ CASE 221D

MARKING DIAGRAM



A = Assembly Location

Y = Year
WW = Work Week
B20200 = Device Code
G = Pb-Free Package
AKA = Polarity Designator

ORDERING INFORMATION

Device	Package	Shipping
MBRF20200CTG	TO-220 (Pb-Free)	50 Units/Rail

1

^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBRF20200CTG

MAXIMUM RATINGS (Per Leg)

Rating			Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	200	V
Average Rectified Forward Current (Rated V_R) $T_C = 125^{\circ}C$	Per Leg Per Package	I _{F(AV)}	10 20	Α
Peak Repetitive Forward Current, Per Leg	(Rated V _R , Square Wave, 20 kHz) T _C = 90°C	I _{FRM}	20	Α
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)			150	Α
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)		I _{RRM}	1.0	Α
Operating Junction Temperature and Storage Temperature		T _J , T _{stg}	-65 to +150	°C
Voltage Rate of Change (Rated V _R)		dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Per Leg)

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case		3.5	°C/W

ELECTRICAL CHARACTERISTICS (Per Leg)

Rating	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1)	٧ _F		V
$(i_F = 10 \text{ Amp}, T_C = 25^{\circ}C)$		0.9	
$(i_F = 10 \text{ Amp}, T_C = 125^{\circ}C)$		8.0	
$(i_F = 20 \text{ Amp}, T_C = 25^{\circ}C)$		1.0	
(i _F = 20 Amp, T _C = 125°C)		0.9	
Maximum Instantaneous Reverse Current (Note 1)	i _R		mA
(Rated dc Voltage, T _C = 25°C)		1.0	
(Rated dc Voltage, T _C = 125°C)		50	

DYNAMIC CHARACTERISTICS (Per Leg)

Capacitance ($V_B = -5.0 \text{ V}$, $T_C = 25^{\circ}\text{C}$, Freq. = 1.0 MHz)	Ст	500	pF
	- 1		F

^{1.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%

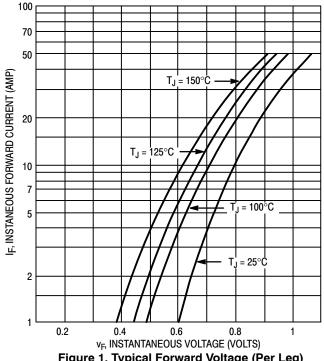


Figure 1. Typical Forward Voltage (Per Leg)

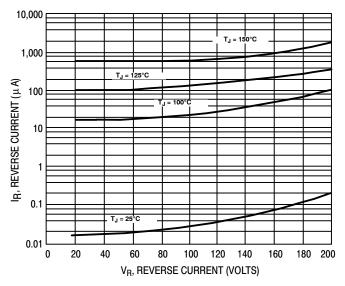


Figure 2. Typical Reverse Current (Per Leg)

MBRF20200CTG

TEST CONDITION FOR ISOLATION TEST*

FULLY ISOLATED PACKAGE

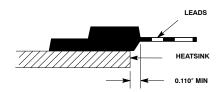
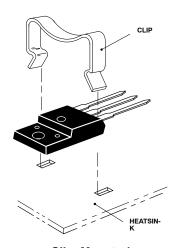


Figure 3. Mounting Position

*Measurement made between leads and heatsink with all leads shorted together.

MOUNTING INFORMATION



Clip-Mounted

Figure 4. Typical Mounting Technique





SCALE 1:1

TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009

0

AYWW

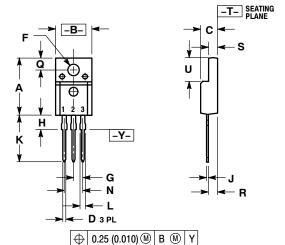
xxxxxxG

AKA

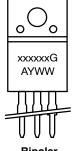
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

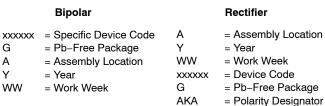
	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.617	0.635	15.67	16.12	
В	0.392	0.419	9.96	10.63	
С	0.177	0.193	4.50	4.90	
D	0.024	0.039	0.60	1.00	
F	0.116	0.129	2.95	3.28	
G	0.100 BSC		0.100 BSC 2.54 BSC		BSC
Н	0.118	0.135	3.00	3.43	
J	0.018	0.025	0.45	0.63	
K	0.503	0.541	12.78	13.73	
L	0.048	0.058	1.23	1.47	
N	0.200 BSC		5.08	BSC	
Q	0.122	0.138	3.10	3.50	
R	0.099	0.117	2.51	2.96	
S	0.092	0.113	2.34	2.87	
U	0.239	0.271	6.06	6.88	

MARKING DIAGRAMS



STYLE 1: PIN 1. GATE STYLE 2: PIN 1. BASE STYLE 3: PIN 1. ANODE 2. COLLECTOR 3. EMITTER CATHODE
 ANODE 2. DRAIN 2. 3. SOURCE STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE STYLE 4: PIN 1. CATHODE STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE ANODE 3. CATHODE





DOCUMENT NUMBER:	98ASB42514B	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TO-220 FULLPAK		PAGE 1 OF 1	

Υ

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales